

# 2SC5346

## Silicon NPN epitaxial planar type

For low-frequency high breakdown voltage amplification  
Complementary to 2SA1982

### ■ Features

- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- High collector-emitter voltage (Base open)  $V_{CEO}$
- Small collector output capacitance (Common base, input open circuited)  $C_{ob}$

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	150	V
Collector-emitter voltage (Base open)	$V_{CEO}$	150	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	50	mA
Peak collector current	$I_{CP}$	100	mA
Collector power dissipation *	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*: Copper plate at the collector is more than  $1\text{ cm}^2$  in area, 1.7 mm in thickness

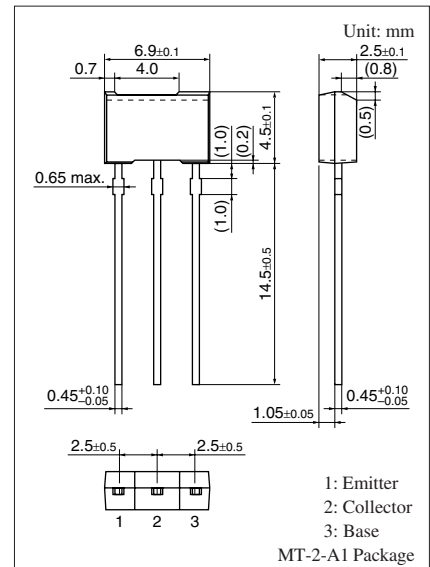
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

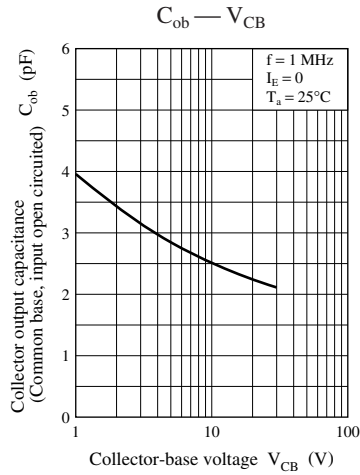
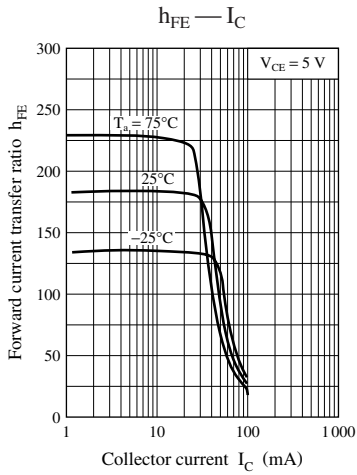
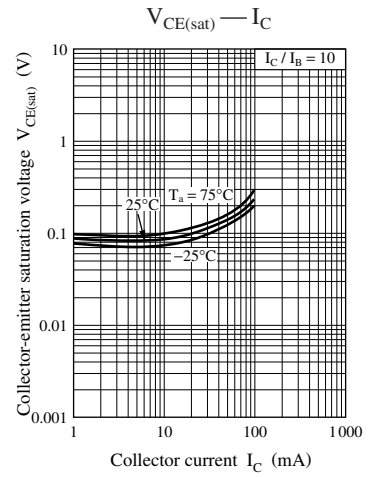
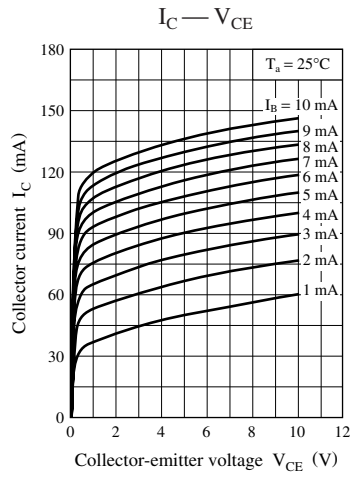
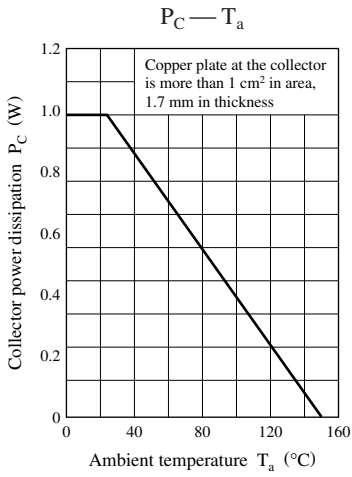
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 0.1\text{ mA}$ , $I_B = 0$	150			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10\ \mu\text{A}$ , $I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 100\text{ V}$ , $I_E = 0$			1	$\mu\text{A}$
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$	130		330	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30\text{ mA}$ , $I_B = 3\text{ mA}$			1	V
Transition frequency	$f_T$	$V_{CB} = 10\text{ V}$ , $I_E = -10\text{ mA}$ , $f = 200\text{ MHz}$		160		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$			5	pF
Noise voltage	NV	$V_{CE} = 10\text{ V}$ , $I_C = 1\text{ mA}$ , $G_V = 80\text{ dB}$ $R_g = 100\text{ k}\Omega$ , Function = FLAT		150	300	mV

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	R	S
$h_{FE}$	130 ~ 220	185 ~ 330





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